



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Kuei-Wu Huang, et al.

U.S. Serial No.

09/517,987

Filed

March 3, 2000

For

METHOD OF FORMING PLANARIZED STRUCTURE
AN INTEGRATED CURCLUM

AN INTEGRATED CIRCUIT

Group No.

2812

Examiner

R. Booth

Commissioner of Patents and Trademarks

Washington, D. C. 20231

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents and Trademarks, Washington, D.C.

Dear Sir:

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT BEFORE MAILING DATE OF EITHER A FINAL ACTION OR NOTICE OF ALLOWANCE (37 CFR 1.97(c))

Time of Transmittal of Accompanying **Information Disclosure Statement**

The Information Disclosure Statement transmitted herewith is being filed after the mailing date of the first Office Action on the merits.

The patents, publications and other information herein are listed below and on the attached Form PTO-1449. Copies of the listed references are submitted herewith.

02/01/2001 HLAKEU1 00000009 0951

100,00 NEWS 00000037 09517907

DOCKET NO. 94-C-096C2 U.S. SERIAL NO. 09/517,987 PATENT

U.S. Patent No.	<u>Inventor</u>	<u>Date</u>
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Publication

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Certification or Fee

- 2. Accompanying this transmittal is
 - a certification as specified in 37 CFR 1.97(e)

OR

X the fee \$180.00 set forth in 37 CFR 1.17(p) for submission of an Information Disclosure Statement under §1.97(c).

Fee Payment

- 3. X Applicant elects the option to pay the fee set forth in 37 CFR 1.17(p) for submission of an Information Disclosure Statement under §1.97(c).
 - X Attached is a check in the amount of \$180.00.
- 4. __ No fee required 37 CFR 1.97(e) Certification enclosed.

Applicant hereby expressly reserves the right to swear behind the effective dates of any of the above Patents and to question the relevance and materiality of the Patents and Publications listed herein, in whole, in part, or in combination, subsequent to filing this Information Disclosure

DOCKET NO. 94-C-096C2 U.S. SERIAL NO. 09/517,987 PATENT

Respectfully submitted,

Registration No. 39,409

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